CMSC5006B

-60V, 54mΩ typ., -15A P-Channel MOSFET

General Description

The CMSC5006B uses advanced trench technology to provide excellent RDS(ON). This device is suitable for use as a load switch or power management.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
-60V	65mΩ	-15A

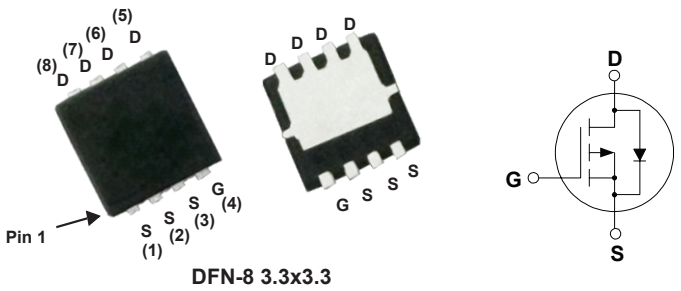
Applications

- DC/DC Conversion
- Load Switches

Features

- P-Channel MOSFET
- Low ON-resistance
- Surface Mount Package
- RoHS Compliant

DFN-8 3.3x3.3 Pin Configuration



DFN-8 3.3x3.3

Type	Package	Marking
CMSC5006B	DFN-8 3.3x3.3	5006B

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	-15	A
I_D@T_C=100℃	Continuous Drain Current	-11	A
I_{DM}	Pulsed Drain Current	-60	A
EAS	Single Pulse Avalanche Energy[1]	40	mJ
P_D@T_C=25℃	Total Power Dissipation	40	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	3.13	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250μA	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-6A	---	54	65	mΩ
		V_{GS}=-4.5V , I_D=-4A	---	61	72	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D = -250μA	-1.0	---	-2.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-60V , V_{GS} =0V	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS} =±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-6A	---	12	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	12.5	---	Ω
Q_g	Total Gate Charge	V_{DS}=-48V , I_D=-15A V_{GS}=-10V	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	3.8	---	
Q_{gd}	Gate-Drain Charge	(Note 2)	---	7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-30V, V_{GS} =-10V I_D= -7.5A , R_G =0Ω (Note 2)	---	7	---	ns
T_r	Rise Time		---	5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	100	---	
T_f	Fall Time		---	65	---	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , f=1MHz	---	1600	---	pF
C_{oss}	Output Capacitance		---	60	---	
C_{rss}	Reverse Transfer Capacitance		---	55	---	

Diode Characteristics

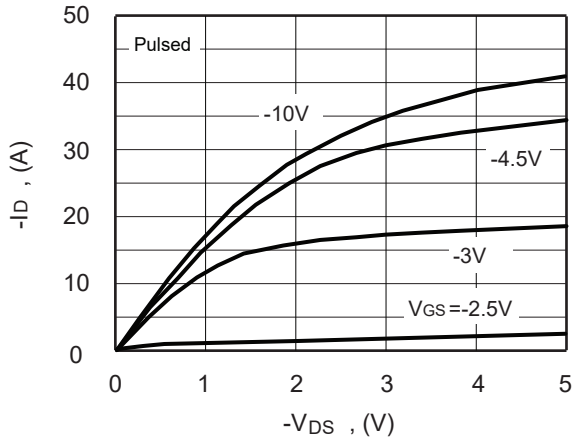
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-15	A
I_{SM}	Pulsed Source Current		---	---	-60	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-5A ,T_J=25℃	---	-0.84	-1.2	V

Note :

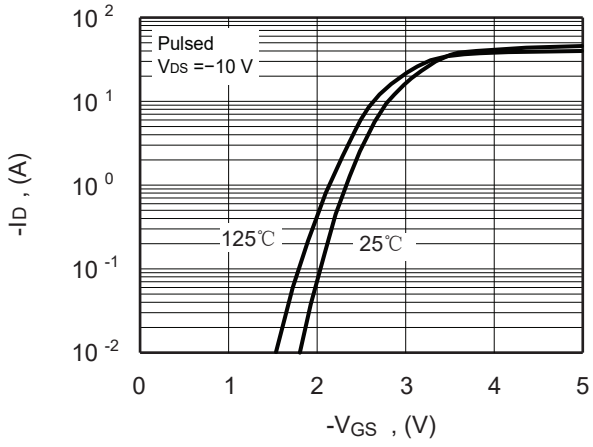
1.The EAS data shows Max. rating . The test condition is V_{DD}=-30V , V_{GS}=-10V , L=0.5mH , I_{AS}=-12.8A.

3. Defined by design, not subject to production.

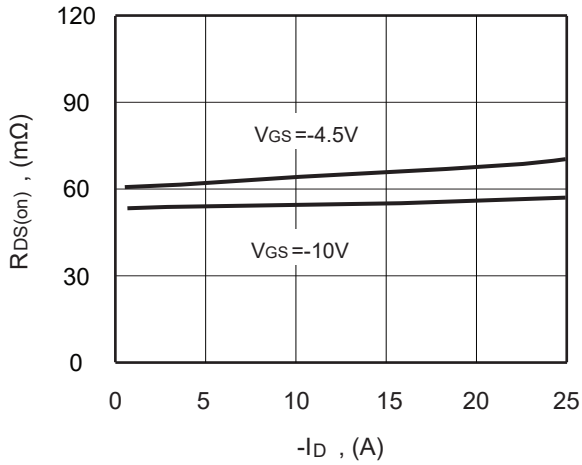
Typical Characteristics



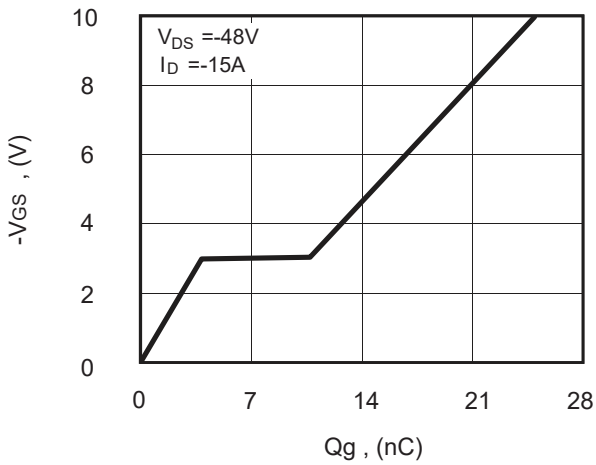
Output Characteristics



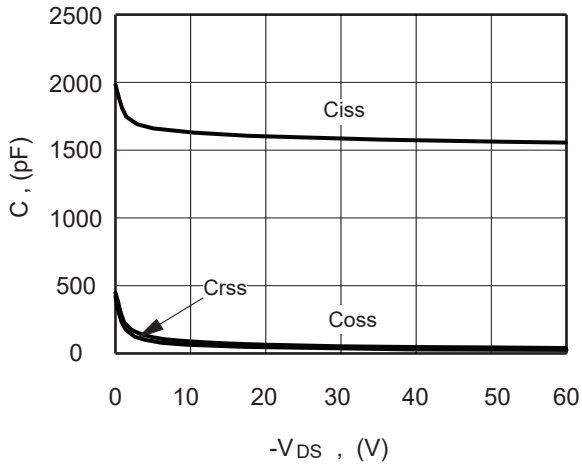
transfer characteristics



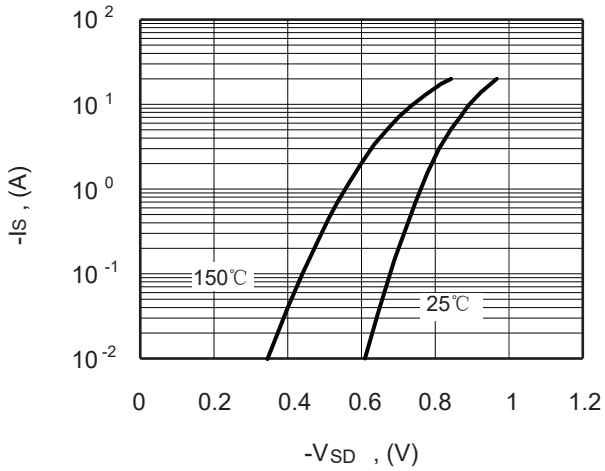
On-Resistance vs. Drain Current



Gate Charge Characteristics



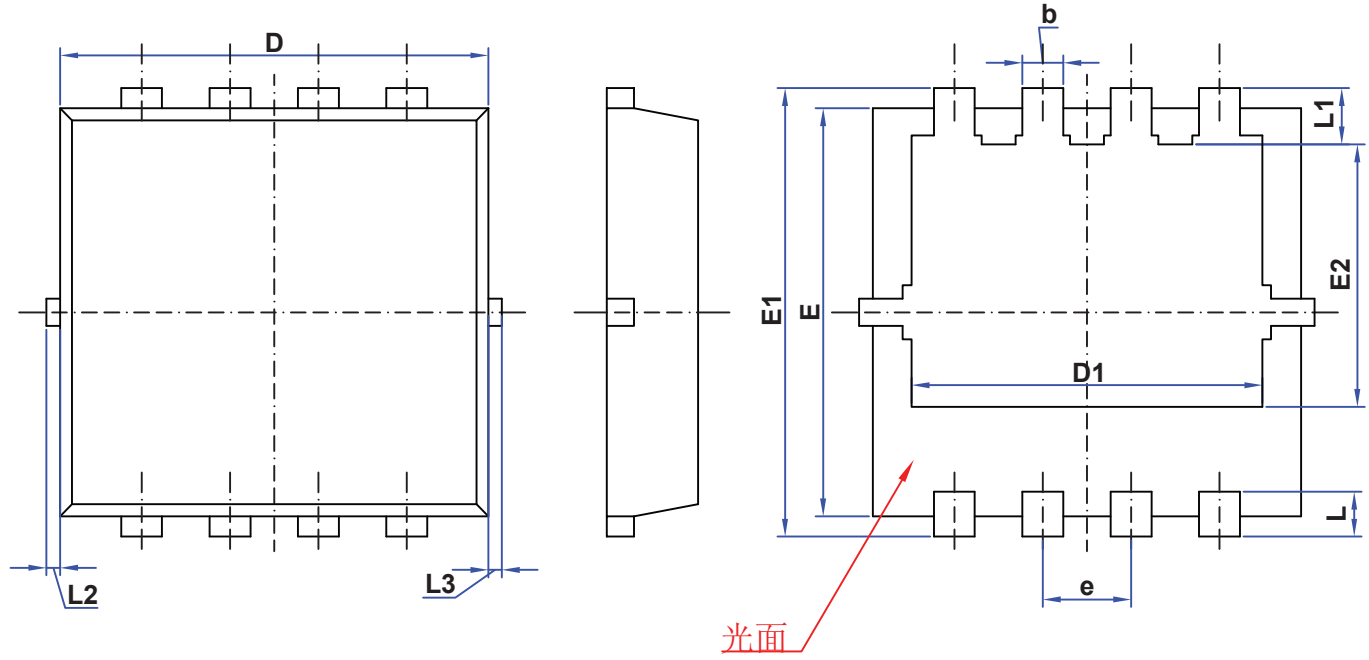
Capacitance Characteristics

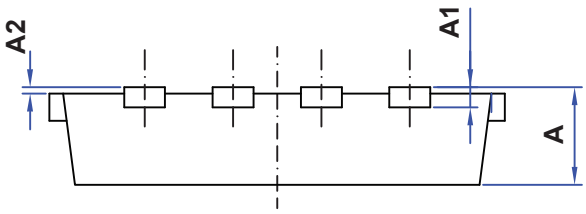


Body-Diode Characteristics

Package Dimension

DFN-8 3.3x3.3 Unit :mm





注：
1.未注公差±0.10,
2.塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
3.标注单位mm

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.700	0.900	0.800
A1	0.100	0.200	0.150
A2	-	0.050	-
D	3.000	3.200	3.100
D1	2.350	2.550	2.450
E	3.000	3.200	3.100
E1	3.200	3.600	3.400
E2	1.635	1.835	1.735
b	0.200	0.400	0.300
e	0.550	0.750	0.650
L	0.250	0.650	0.450
L1	0.345	0.745	0.545
L2	0~0.100		
L3	0~0.100		